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April 16, 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):

NOGUCHI et al.

Serial No.:

09/825,946

Filed:

April 5, 2001

For:

SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND

FABRICATION METHOD FOR SEMICONDUCTOR

INTEGRATED CIRCUIT DEVICE

Group:

2811

Examiner:

H. Vu

AMENDMENT AFTER FINAL REJECTION

Assistant Commissioner

for Patents

Washington, D.C. 20231

Sir:

In response to the Office Action of November 20, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel Claims 24 and 28.

Please amend Claim 20, 25, 26, 29, - 31 as follows:

20. (twice amended) A method of fabricating a semiconductor integrated circuit device comprising:

(a) providing a semiconductor substrate having a first main surface,